

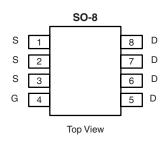
N-Channel 150-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
150	0.085 at V _{GS} = 10 V	3.7		
	0.095 at V _{GS} = 6.0 V	3.5		

FEATURES

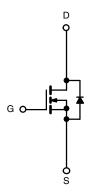
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4848DY-T1-E3 (Lead (Pb)-free)

Si4848DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise n	oted		_
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	150		V
Gate-Source Voltage		V_{GS}	± 20		V
O	T _A = 25 °C	1	3.7	2.7	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	l _D	3.0	2.1	
Pulsed Drain Current		I _{DM}	25		Α
Avalanche Current	L = 0.1 mH	I _{AS}	10		
Continuous Source Current (Diode Conduction) ^a		I _S	2.5	1.3	
M	T _A = 25 °C	P _D	3.0	1.5	W
Maximum Power Dissipation ^a	T _A = 70 °C	гD	1.9	1.0	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 1	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestor Location to Applicated	t ≤ 10 s	R _{thJA}	35	42	
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	68	82	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	18	23	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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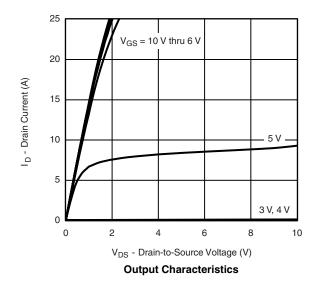
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Test Conditions Min.		Max.	Unit	
Parameter Symbol Test Conditions Min. Typ. Max. Unit Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ 2.0				V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			± 100	nA	
Zero Coto Valtono Duoin Comunit	1	V _{DS} = 120 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 120 V, V_{GS} = 0 V, T_{J} = 55 °C			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	25			Α	
	В	V _{GS} = 10 V, I _D = 3.5 A	0.068 0.08		0.085		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 6.0 \text{ V}, I_D = 3.0 \text{ A}$		0.076	0.095	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 5 A		15		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 2.5 A, V _{GS} = 0 V		0.75	1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			17	21		
Gate-Source Charge	Q_{gs}	Q_{gs} $V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$		3.2		nC	
Gate-Drain Charge	Q_{gd}			6.0			
Gate Resistance	R_{g}		0.5	0.85	1.8	Ω	
Turn-On Delay Time	t _{d(on)}			9.0	14		
Rise Time	t _r	V_{DD} = 75 V, R_L = 21 Ω		10	15		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 3.5 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		24	35	ns	
Fall Time	t _f			17	25		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.5 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		45	70		

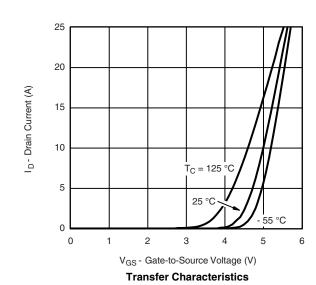
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



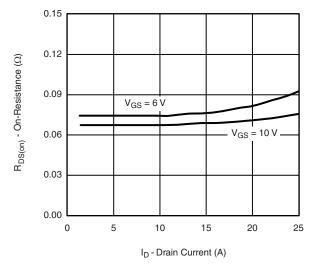




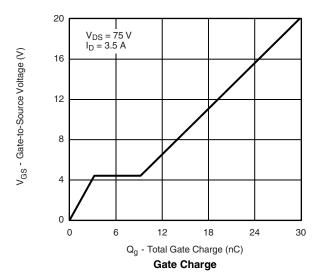


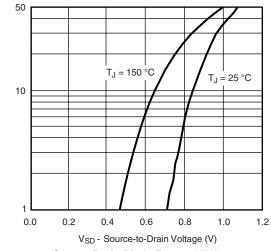


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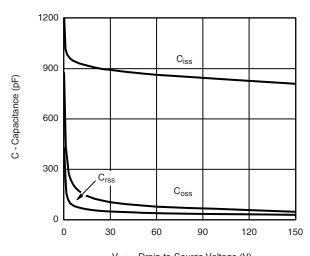


On-Resistance vs. Drain Current



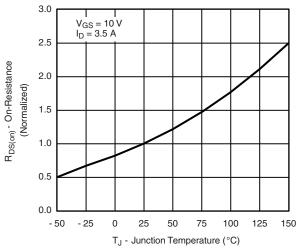


Source-Drain Diode Forward Voltage

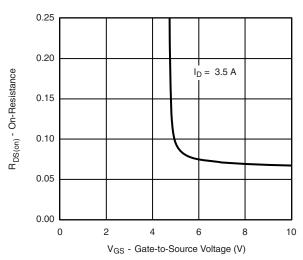


V_{DS} - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature

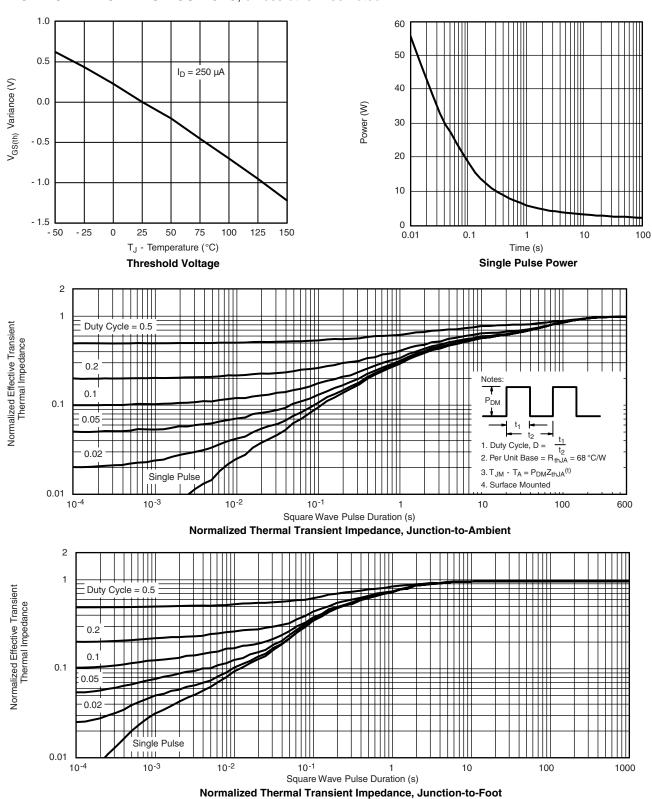


Is - Source Current (A)

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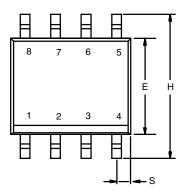
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	INCHES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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